



AF/2814  
IFW

Docket No.: M4065.0210/P210-A  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Sam Yang, et al.

Examiner: Vikki Trinh

Application No.: 10/002,176

Art Unit: 2814

Filed: December 5, 2001

For: IMPROVED MEMORY CELL CAPACITOR  
STRUCTURE AND METHOD OF  
FORMATION

AMENDMENT AFTER FINAL ACTION (37 C.F.R. SECTION 1.116)

Commissioner for Patents  
MS: AF  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

This paper is in response to the Office Action dated June 1, 2004. Please amend the above-identified U.S. patent application as follows:

**Amendment to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Remarks** begin on page 10 of this paper.